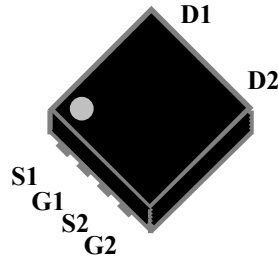




- ▼ Simple Drive Requirement
- ▼ Good Thermal Performance
- ▼ Fast Switching Performance
- ▼ RoHS Compliant & Halogen-Free

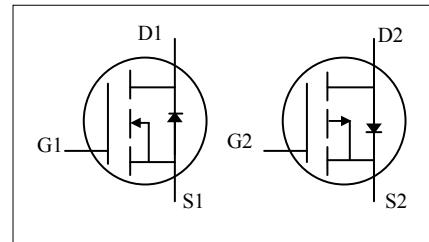


**PMPAK<sup>®</sup> 3x3**

N-CH	$BV_{DSS}$	30V
	$R_{DS(ON)}$	17.8m $\Omega$
P-CH	$BV_{DSS}$	-30V
	$R_{DS(ON)}$	30m $\Omega$

**Description**

AP3C017A series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



The PMPAK<sup>®</sup> 3x3 package is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal performance.

**Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
$V_{DS}$	Drain-Source Voltage	30	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_C=25^\circ C$	Drain Current, $V_{GS}$ @ 10V	20.8	-16.7	A
$I_D@T_C=100^\circ C$	Drain Current, $V_{GS}$ @ 10V	13	-10.6	A
$I_D@T_A=25^\circ C$	Drain Current <sup>3</sup> , $V_{GS}$ @ 10V	9.3	-7.5	A
$I_D@T_A=70^\circ C$	Drain Current <sup>3</sup> , $V_{GS}$ @ 10V	7.4	-6	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	-30	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.5		W
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

**Thermal Data**

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	10	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	$^\circ C/W$



# AP3C017AYT

## N-CH Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =9A	-	-	17.8	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	-	27	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.4	-	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =9A	-	22	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =5A	-	10	16	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V	-	4	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	3	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15V	-	9	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	7	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	21	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	5	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1200	1920	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V	-	120	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	100	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =9A, V <sub>GS</sub> =0V	-	10	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	4	-	nC

**P-CH Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-7A	-	-	30	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	-	-	57	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.4	-	-2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-7A	-	12	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V	-	-	+100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =-5A	-	9	14.4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-15V	-	4	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	3	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-15V	-	11	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-1A	-	6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	30	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =-10V	-	8	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1000	1600	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V	-	140	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	100	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-2A, V <sub>GS</sub> =0V	-	-	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =-7A, V <sub>GS</sub> =0V,	-	11	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	4	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t ≤10sec, 90°C/W at steady state.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.



## N-Channel

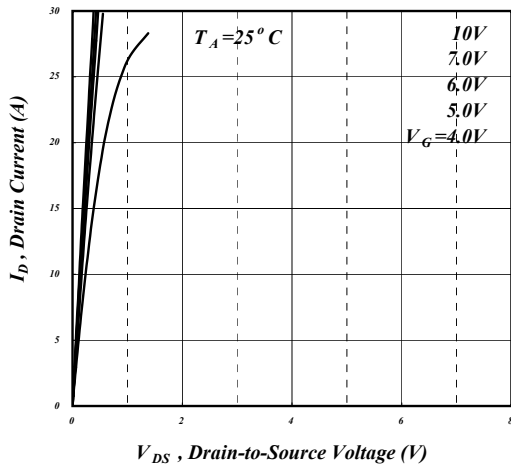


Fig 1. Typical Output Characteristics

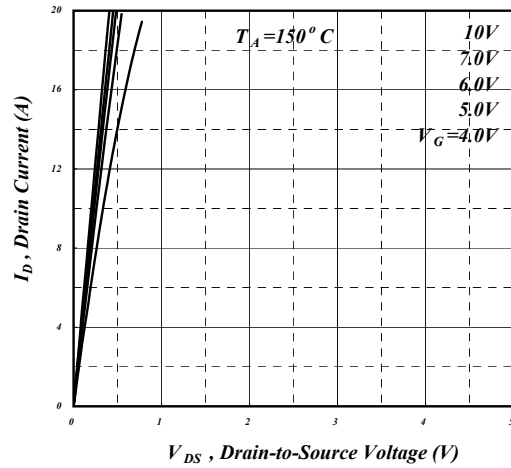


Fig 2. Typical Output Characteristics

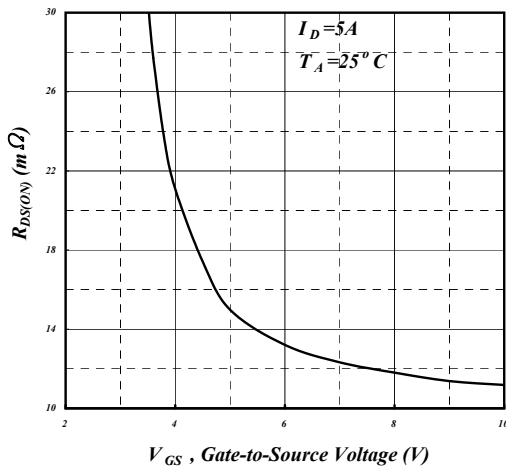


Fig 3. On-Resistance vs. Gate Voltage

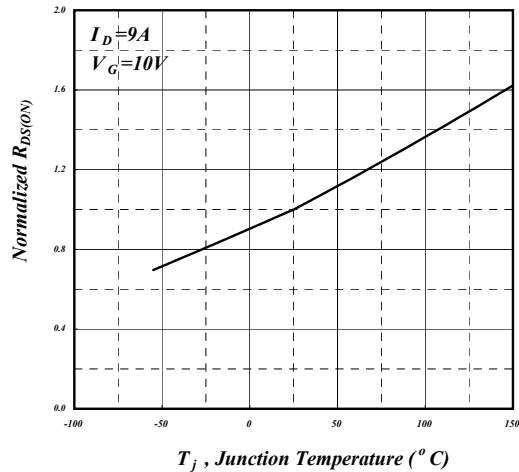


Fig 4. Normalized On-Resistance vs. Junction Temperature

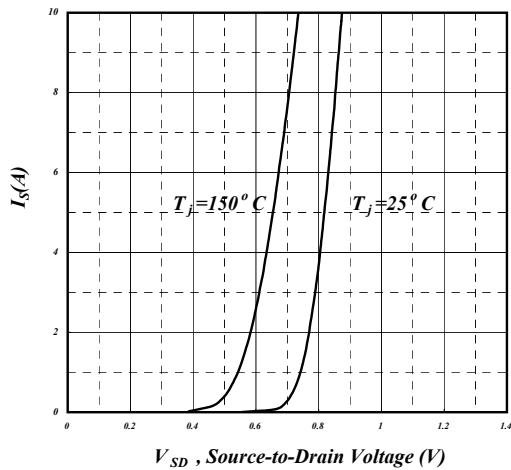


Fig 5. Forward Characteristic of Reverse Diode

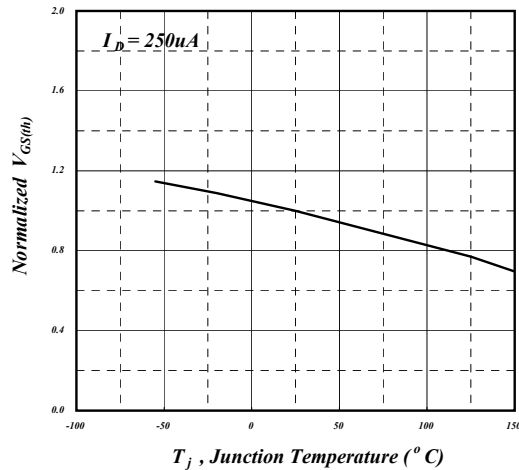


Fig 6. Gate Threshold Voltage vs. Junction Temperature



N-Channel

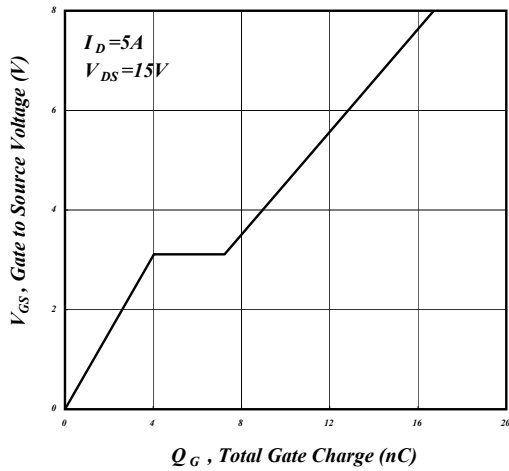


Fig 7. Gate Charge Characteristics

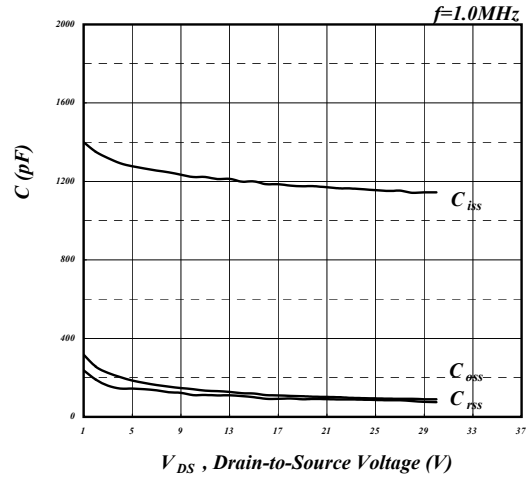


Fig 8. Typical Capacitance Characteristics

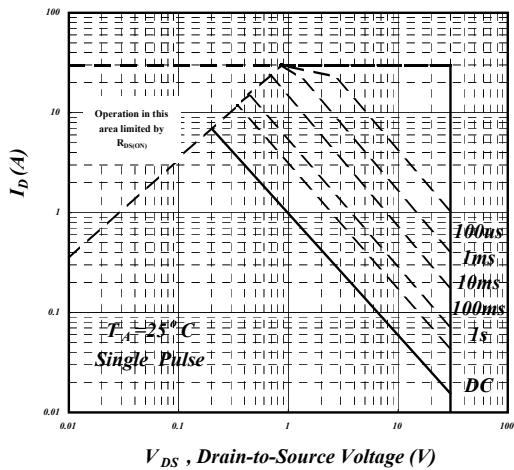


Fig 9. Maximum Safe Operating Area

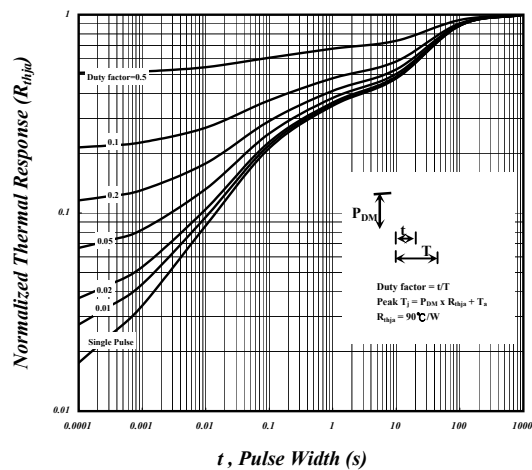


Fig 10. Effective Transient Thermal Impedance

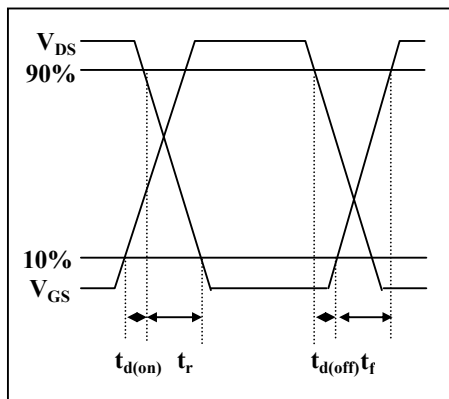


Fig 11. Switching Time Waveform

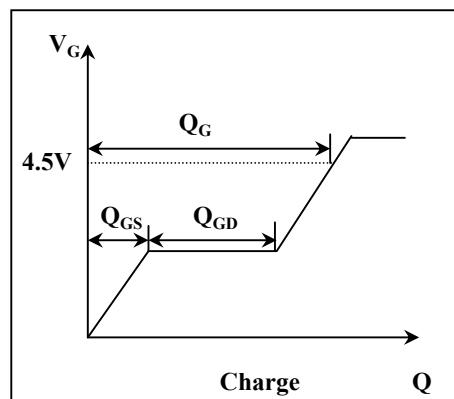


Fig 12. Gate Charge Waveform



# AP3C017AYT

## P-Channel

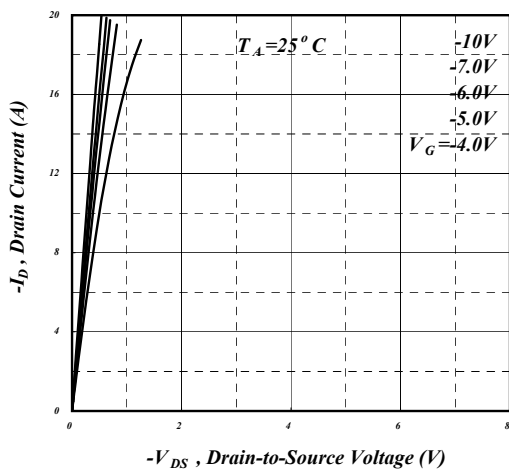


Fig 1. Typical Output Characteristics

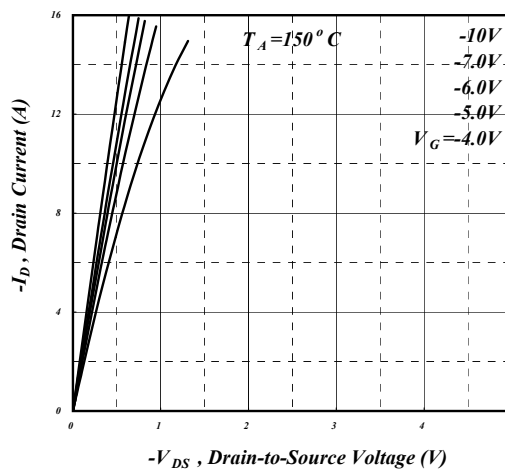


Fig 2. Typical Output Characteristics

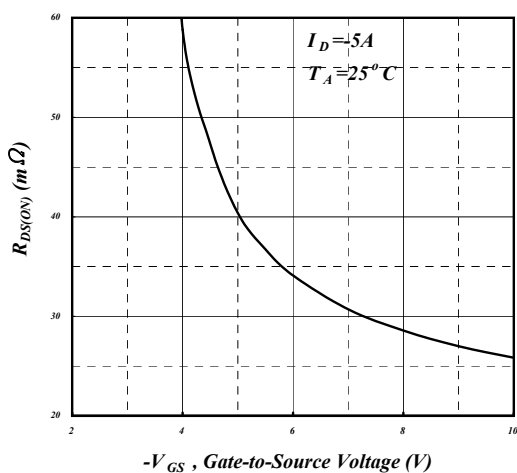


Fig 3. On-Resistance v.s. Gate Voltage

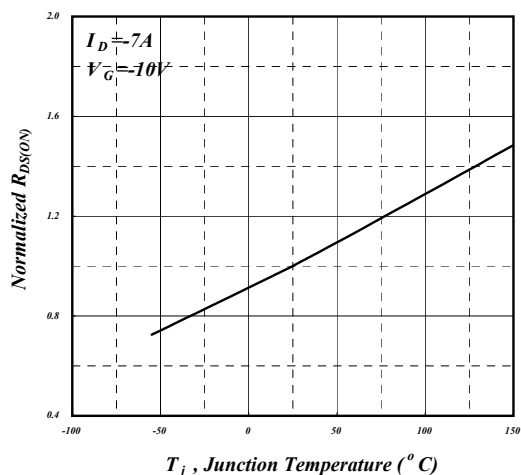


Fig 4. Normalized On-Resistance v.s. Junction Temperature

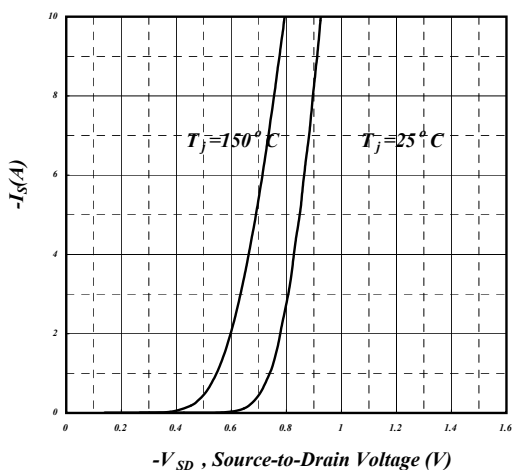


Fig 5. Forward Characteristic of Reverse Diode

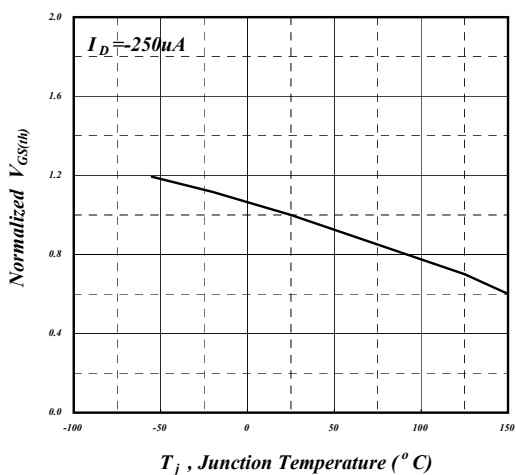


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



P-Channel

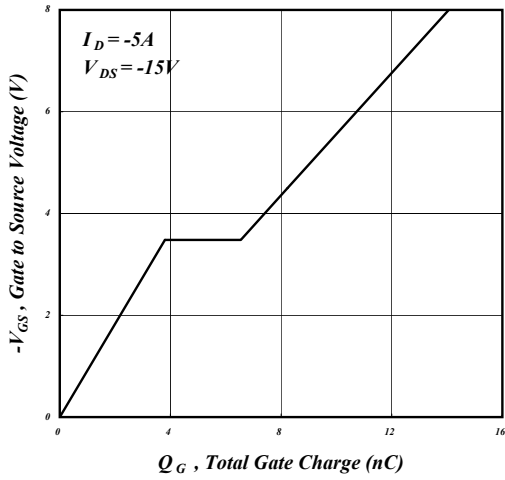


Fig 7. Gate Charge Characteristics

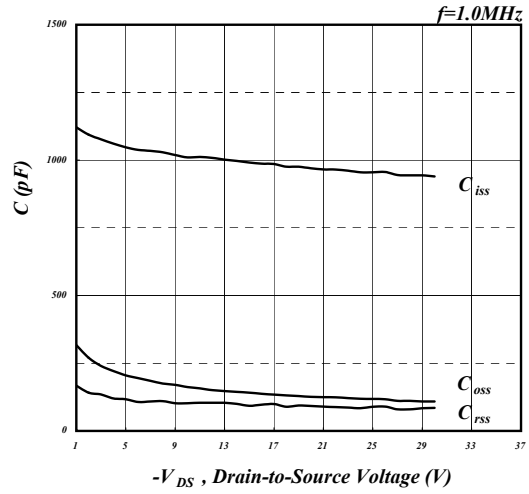


Fig 8. Typical Capacitance Characteristics

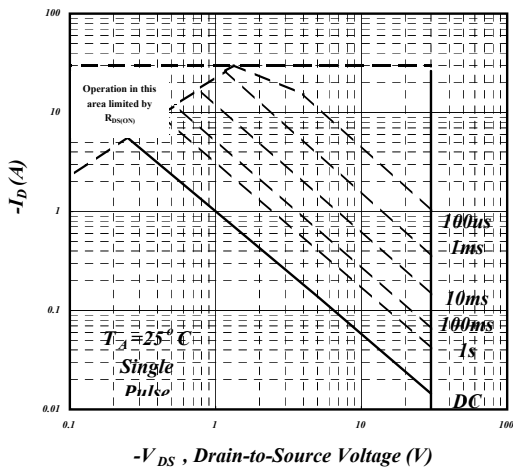


Fig 9. Maximum Safe Operating Area

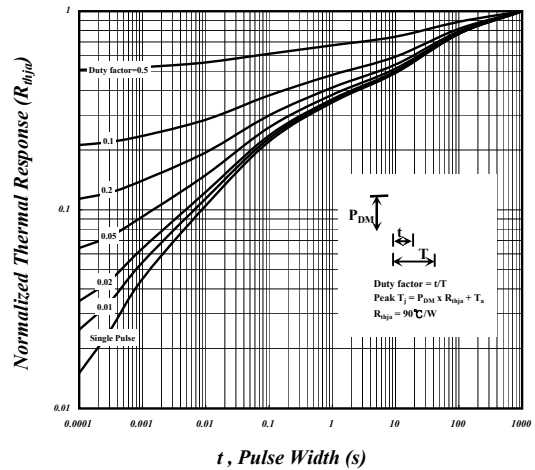


Fig 10. Effective Transient Thermal Impedance

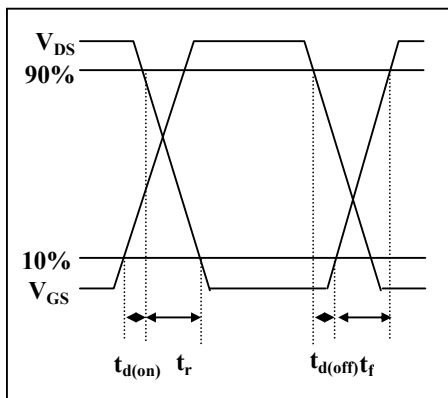


Fig 11. Switching Time Waveform

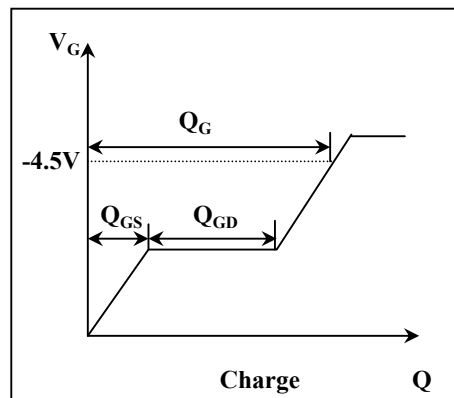


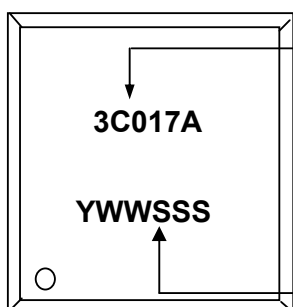
Fig 12. Gate Charge Waveform



**AP3C017AYT**

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**MARKING INFORMATION**



Part Number

**3C017A**

**YWWSSS**

Date Code (YWWSSS)

Y : Last Digit Of The Year

WW : Week

SSS : Sequence